



1SS400

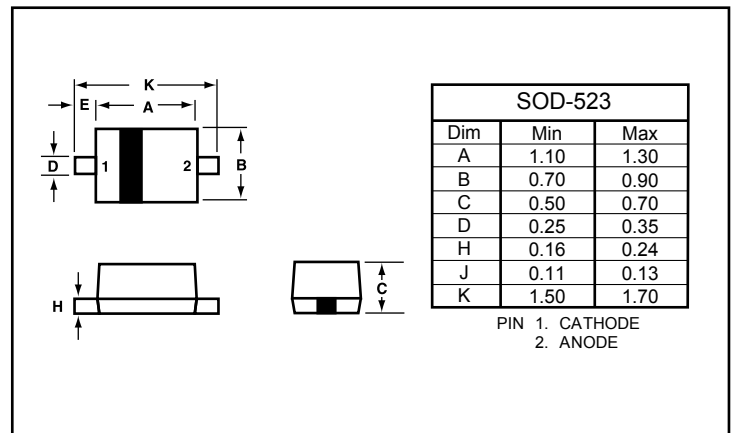
SURFACE MOUNT FAST SWITCHING DIODE

Features

- Extremely fast reverse recovery time to reduce switching losses
- Very low capacitance for reduced insertion losses
- Reverse voltage rating of 80V
- Also available in lead-free plating (100% matte tin finish)

APPLICATION

- Mobile phones and accessories
- Hand-held computers
- High Speed Switching Applications



Maximum Ratings @T_A=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	90	V
DC Reverse voltage	V _R	80	V
Continuous forward current	I _F	225	mA
Surge current	I _{FSM}	0.5	A
Total power dissipation	P _{tot}	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55-150	°C

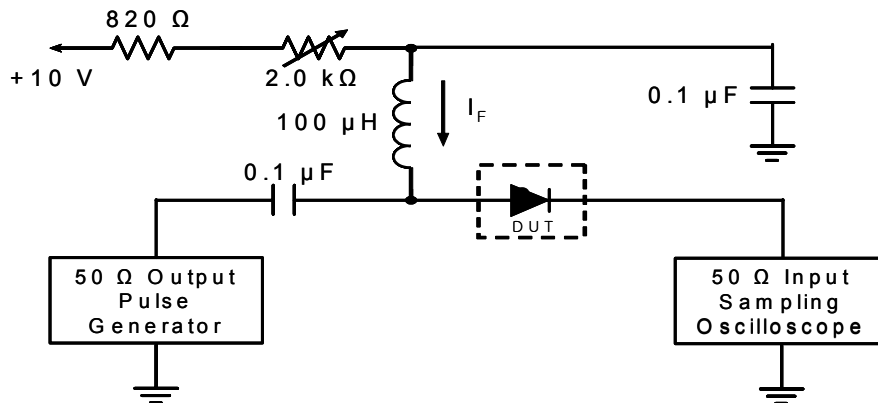
Electrical Characteristics @T_A=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			1.2	V	I _F =100mA
Reverse current	I _R			0.1	μA	V _R =80V
Diode capacitance	C _d		0.72	2.0	pF	V _R =0.5V, f=1MHz
Reverse recovery time	t _{rr}			4	ns	V _R =6V, I _F =10mA, R _L =100Ω



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RATINGS AND CHARACTERISTIC CURVES



- Notes: 1. A 2.0kΩ variable resistor adjusted for a forward current (I_F) to 10mA
2. Input pulse is adjusted to $I_{R(peak)}$ is equal to 10mA

Figure 1. REVERSE RECOVERY TIME EQUIVALENT TEST CIRCUIT

